



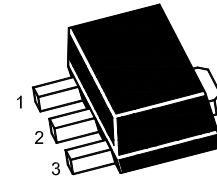
2SB1132SQ

PNP Transistor

Features

- Low saturation voltage

SOT-89



1. Base 2. Collector 3. Emitter

Marking: 1132P
1132Q
1132R

Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	32	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	1	A
Pulsed Collector Current	$-I_{CP}$	2	A
Power Dissipation	P_D	500	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to 150	°C

Electrical Characteristics

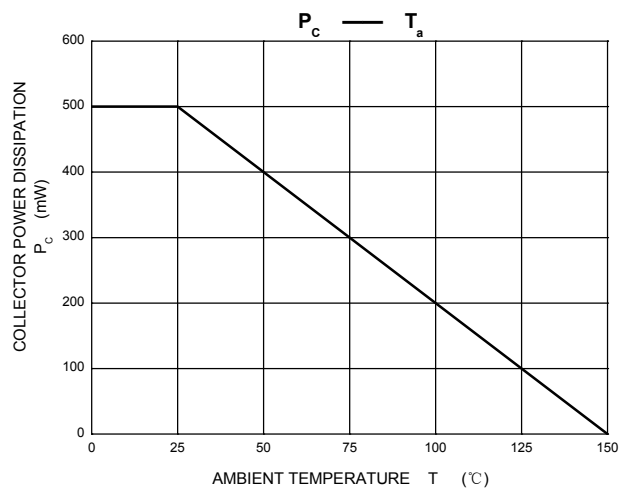
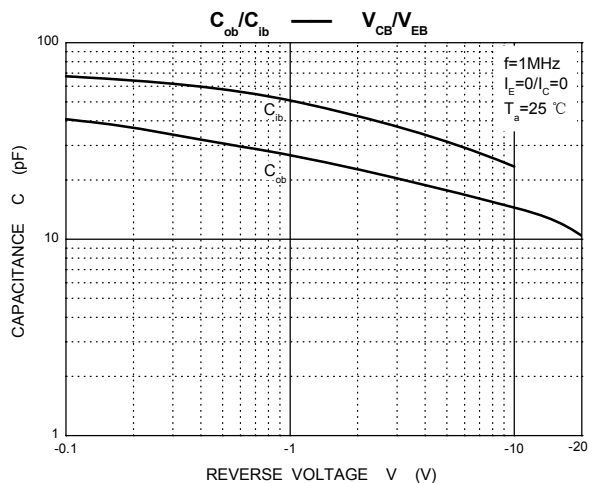
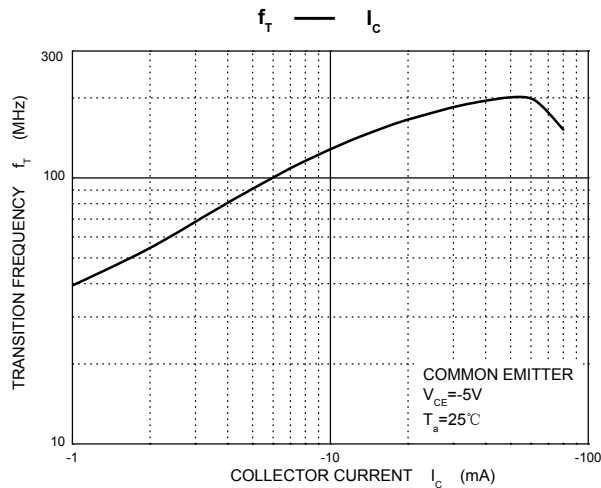
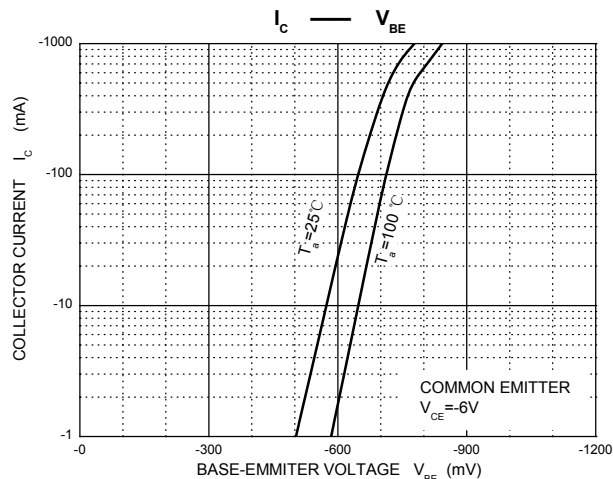
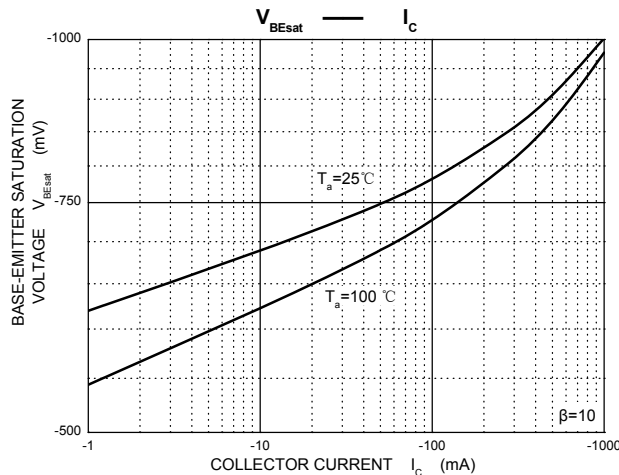
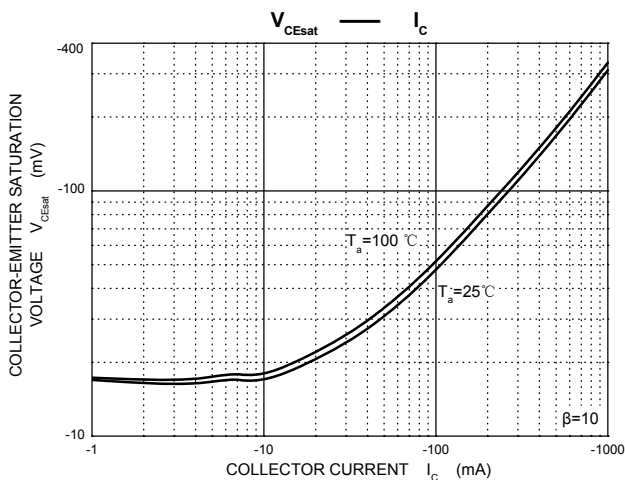
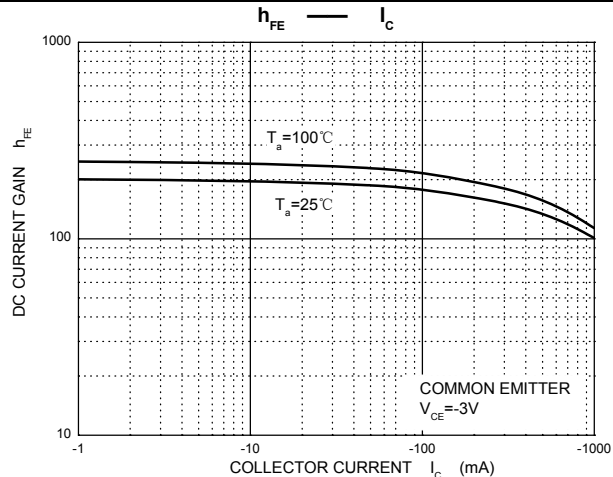
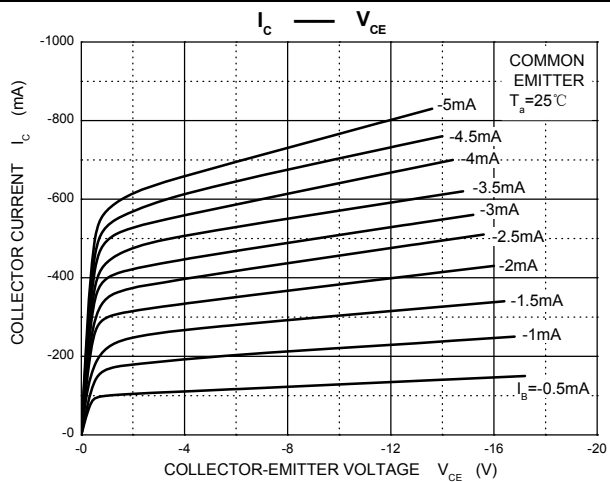
Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 500\text{ mA}$ Current Gain Group	H_{FE}	82 120 180	- - -	180 270 390	-
Collector Base Cutoff Current at $-V_{CB} = 20\text{ V}$	$-I_{CBO}$	-	-	0.5	μA
Emitter Base Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	-	0.5	μA
Collector Base Breakdown Voltage at $-I_C = 50\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	32	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 50\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	0.2	0.5	V
Transition Frequency at $-V_{CE} = 5\text{ V}$, $-I_C = 50\text{ mA}$, $f = 30\text{ MHz}$	f_T	-	150	-	MHz
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	C_{ob}	-	20	30	pF



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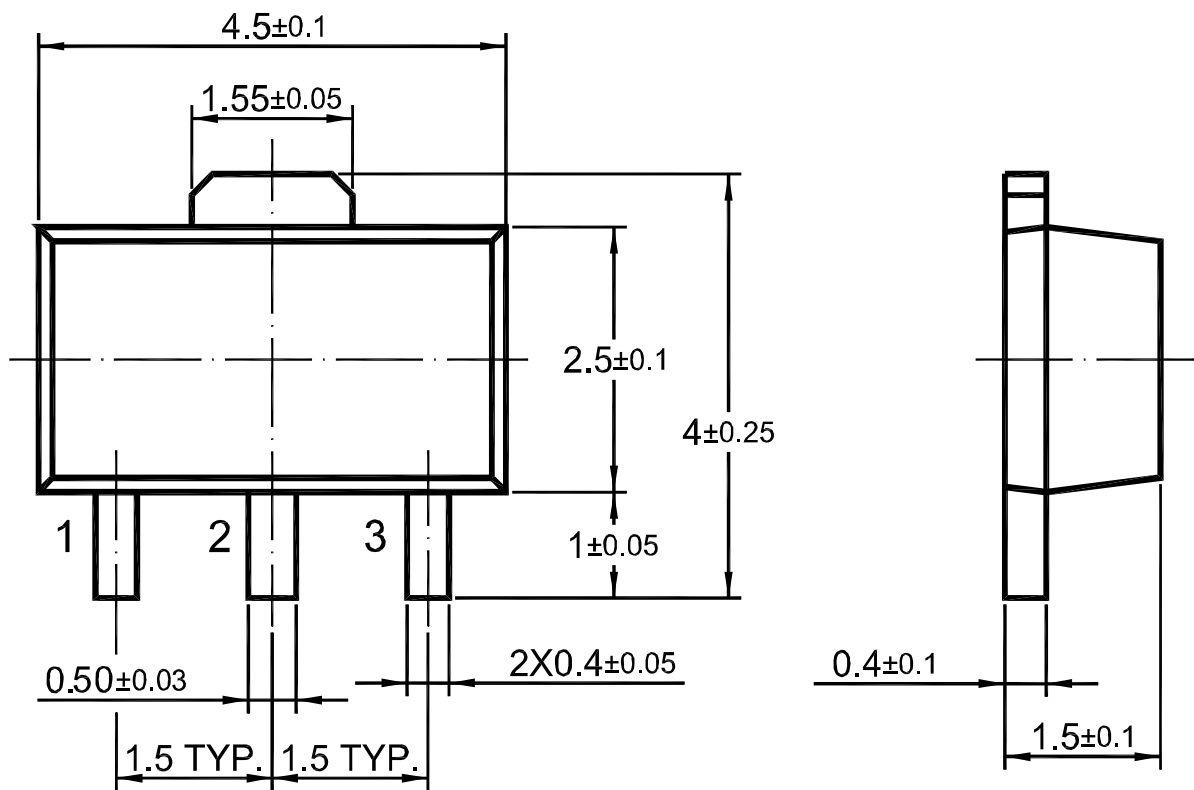




Package Outline

SOT-89

Dimensions in mm



Ordering information

Device	Package	Shipping
2SB1132SQ	SOT-89	1000/Tape&Reel(7inches)